TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC3122

TV VHF RF Amplifier Applications

• High gain: Gpe = 24dB (typ.) (f = 200 MHz)

• Low noise: NF = 2.0dB (typ.) (f = 200 MHz)

• Excellent forward AGC characteristics

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	3	٧
Collector current	IC	20	mA
Base current	ΙΒ	10	mA
Collector power dissipation	P _C	150	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

1. BASE 2. EMITTER 3. COLLECTOR JEDEC — JEITA SC-59 TOSHIBA 2-3F1A

Weight: 0.012 g (typ.)

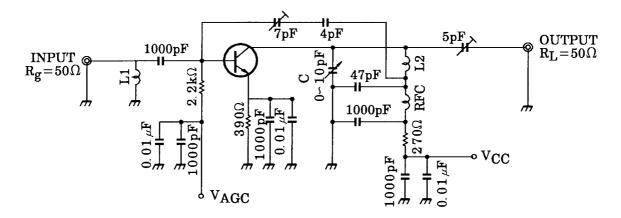
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 25 V, I _E = 0	_	_	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 2 V, I _C = 0	_	_	100	nA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 1 mA, I _B = 0	30	_	_	V
DC current gain	h _{FE}	V _{CE} = 10 V, I _C = 2 mA	60	150	300	
Reverse transfer capacitance	C _{re}	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	0.3	0.45	pF
Transition frequency	f _T	V _{CE} = 10 V, I _C = 2 mA	400	650	_	MHz
Power gain	G _{pe}	V 12 V V 1 4 V f 200 MHz	20	24	28	dB
Noise figure	NF	$V_{CE} = 12 \text{ V}, V_{AGC} = 1.4 \text{ V}, f = 200 \text{ MHz}$	_	2.0	3.2	dB
AGC voltage	V _{AGC}	V _{CC} = 12 V, GR = 30dB, f = 200 MHz (Note)	3.6	4.4	5.1	V

Note: V_{AGC} measured by test circuit shown in Figure 1 when power gain is reduced to 30dB compared that of V_{AGC} at 1.4 V.

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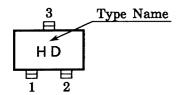
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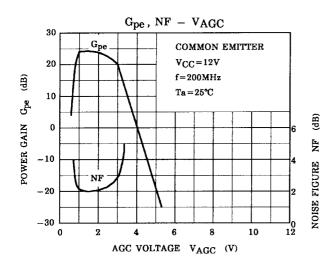


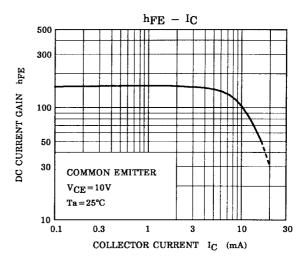
L1: RF Coil M-15 T (TOKO Inc.) or equivalent L2: RF Coil M-25 T (TOKO Inc.) or equivalent

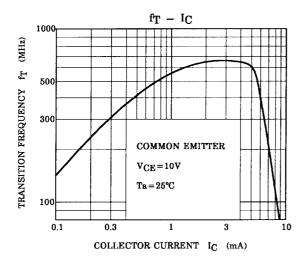
Figure 1 200 MHz Gpe, NF Test Circuit

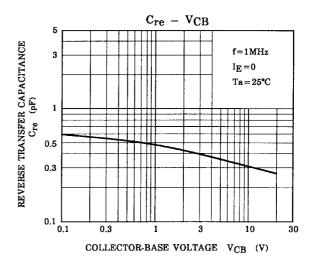
Marking

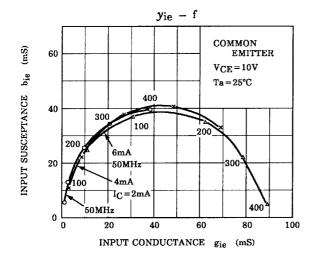


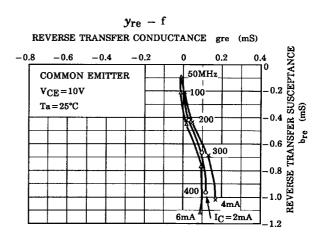


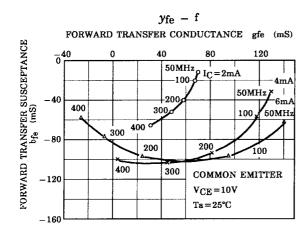


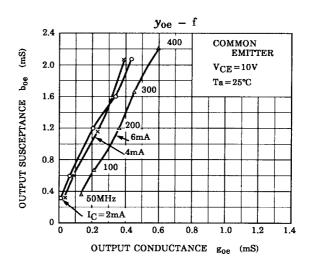


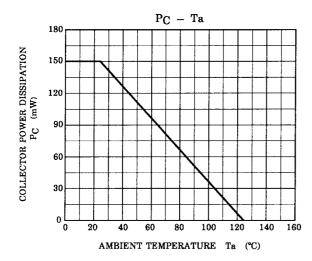












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